

PSMN2R0-30BL

N-channel 30 V 2.1 mΩ logic level MOSFET in D2PAK Rev. 1 — 20 March 2012 Product of

Product data sheet

1. **Product profile**

1.1 General description

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|--|---|-----|-----|------|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 30 | V |
| I_{D} | drain current | $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$ | [1] | - | - | 100 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | | - | - | 211 | W |
| Tj | junction temperature | | | -55 | - | 175 | °C |
| Static char | acteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see <u>Figure 12</u> ; see <u>Figure 11</u> | | - | 2.51 | 2.9 | mΩ |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 11</u> | | - | 1.79 | 2.1 | mΩ |
| Dynamic c | haracteristics | | | | | | |
| Q_{GD} | gate-drain charge | $V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 15 \text{ V};$ | | - | 16 | - | nC |
| Q _{G(tot)} | total gate charge | see Figure 13; see Figure 14 | | - | 55 | - | nC |
| Avalanche | ruggedness | | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω ; unclamped | | - | - | 555 | mJ |

^[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

| | | , | | |
|-----|--------|-----------------------------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | | _ |
| 2 | D | drain[1] | mb | D |
| 3 | S | source | | |
| mb | D | mounting base; connected to drain | | mbb076 S |
| | | | SOT404 (D2PAK) | |

^[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|--------------|---------|--|---------|
| | Name | Description | Version |
| PSMN2R0-30BL | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 |

4. Marking

Table 4. Marking codes

| Type number | Marking code |
|--------------|--------------|
| PSMN2R0-30BL | PSMN2R0-30BL |

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|---|------------|-----|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | 30 | V |
| V_{DGR} | drain-gate voltage | $T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ | | - | 30 | V |
| V_{GS} | gate-source voltage | | | -20 | 20 | V |
| I _D | drain current | $V_{GS} = 10 \text{ V; } T_{mb} = 100 \text{ °C; see } \frac{\text{Figure 1}}{}$ | <u>[1]</u> | - | 100 | Α |
| | | $V_{GS} = 10 \text{ V; } T_{mb} = 25 \text{ °C; see } \frac{\text{Figure 1}}{\text{Model}}$ | [1] | - | 100 | Α |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$; see Figure 3 | | - | 943 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | | - | 211 | W |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |
| $T_{sld(M)}$ | peak soldering temperature | | | - | 260 | °C |
| Source-dra | ain diode | | | | | |
| Is | source current | T _{mb} = 25 °C | [1] | - | 100 | Α |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 943 | Α |
| Avalanche | ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω; unclamped | | - | 555 | mJ |
| | | | | | | |

[1] Continuous current is limited by package.

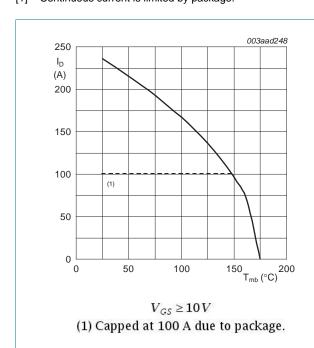


Fig 1. Normalized continuous drain current as a function of mounting base temperature

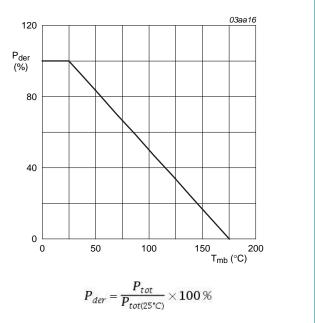
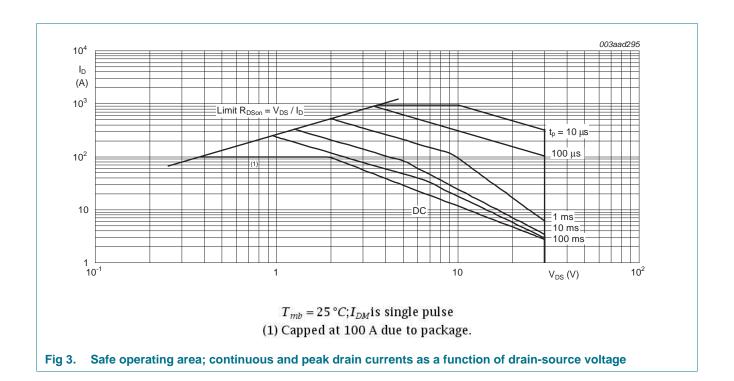


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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Product data sheet

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6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------|---|--|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 4 | - | 0.41 | 0.71 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | maximum foot print; mounted on a printed circuit board | - | 50 | - | K/W |

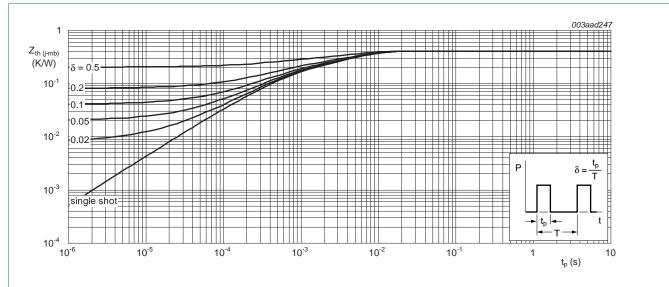


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

7. Characteristics

Table 7. Characteristics

Tested to JEDEC standards where applicable.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------|-----------------------------------|--|-----|------|------|------|
| Static cha | racteristics | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | 30 | - | - | V |
| | | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$ | 27 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see Figure 9; see Figure 10 | 1.3 | 1.7 | 2.15 | V |
| | | $I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 10 | 0.5 | - | - | V |
| | | $I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 10 | - | - | 2.45 | V |
| I _{DSS} | drain leakage current | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.02 | 3 | μΑ |
| | | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$ | - | - | 70 | μΑ |
| I _{GSS} | gate leakage current | $V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 10 | 100 | nΑ |
| | | $V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 10 | 100 | nΑ |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 4.5 V; I_{D} = 25 A; T_{j} = 25 °C; see <u>Figure 11</u> | - | 2.47 | 2.9 | mΩ |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12; see Figure 11 | - | 3.4 | 4 | mΩ |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12; see Figure 11 | - | 2.51 | 2.9 | mΩ |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11 | - | 1.79 | 2.1 | mΩ |
| R _G | gate resistance | f = 1 MHz | - | 0.78 | - | Ω |
| Dynamic o | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$ | - | 107 | - | nC |
| | | $I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 13; see Figure 14 | - | 117 | - | nC |
| | | $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ | - | 55 | - | nC |
| Q _{GS} | gate-source charge | see Figure 13; see Figure 14 | - | 17 | - | nC |
| Q _{GS(th)} | pre-threshold gate-source charge | | - | 11 | - | nC |
| Q _{GS(th-pl)} | post-threshold gate-source charge | | - | 6 | - | nC |
| Q_{GD} | gate-drain charge | | - | 16 | - | nC |
| $V_{GS(pl)}$ | gate-source plateau voltage | $I_D = 25 \text{ A}$; $V_{DS} = 25 \text{ V}$; see <u>Figure 13</u> ; see <u>Figure 14</u> | - | 2.6 | - | V |
| C _{iss} | input capacitance | V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz; | - | 6810 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C; see <u>Figure 15</u> | - | 1410 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 650 | - | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 15 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$ | - | 63 | - | ns |
| t _r | rise time | $R_{G(ext)} = 4.7 \Omega$ | - | 125 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 111 | - | ns |
| | fall time | | | 59 | | ns |

 Table 7.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-----------------------|--|-----|------|-----|------|
| Source-dr | ain diode | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 16</u> | - | 0.76 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; | - | 49 | - | ns |
| Q _r | recovered charge | $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ | - | 66 | - | nC |

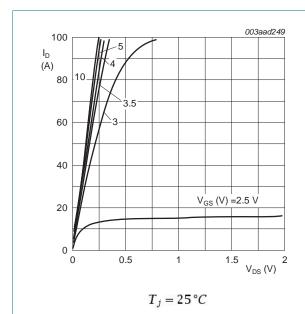


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

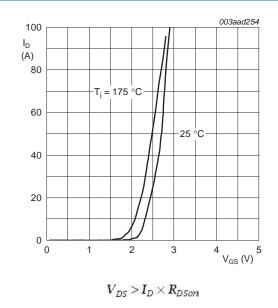


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

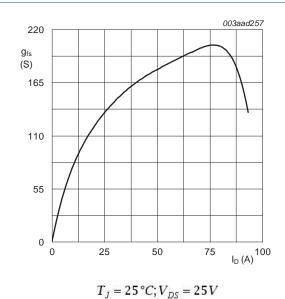
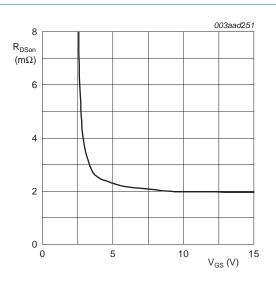


Fig 7. Forward transconductance as a function of drain current; typical values



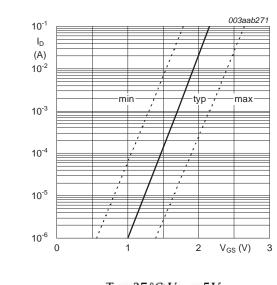
 $T_j=25\,^{\circ}C; I_D=15A$

Fig 8. Drain source on-state resistance as a function of gate-source voltage; typical values

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 $T_j=25\,^{\circ}C; V_{DS}=5\,V$

Fig 9. Sub-threshold drain current as a function of gate-source voltage

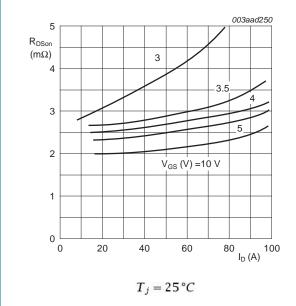
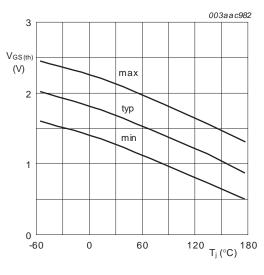


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 1mA; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

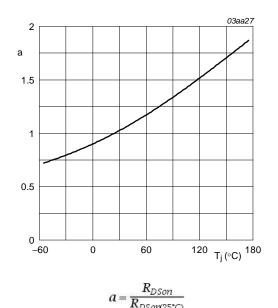
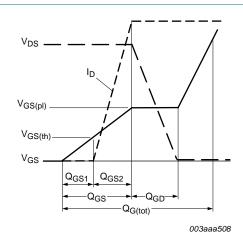


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

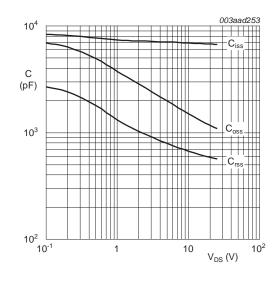


10 003aad255 V_{GS} (V) 8 V_{DS} = 15V 6 4 2 Q_G (nC) 120

 $T_j = 25\,^{\circ}C; I_D = 25A$

Fig 13. Gate charge waveform definitions





 $V_{GS} = 0V; f = 1MHz$

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

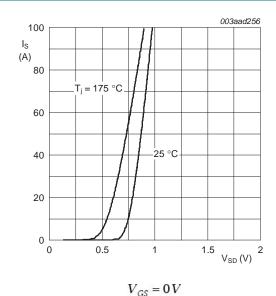


Fig 16. Source current as a function of source-drain voltage; typical values

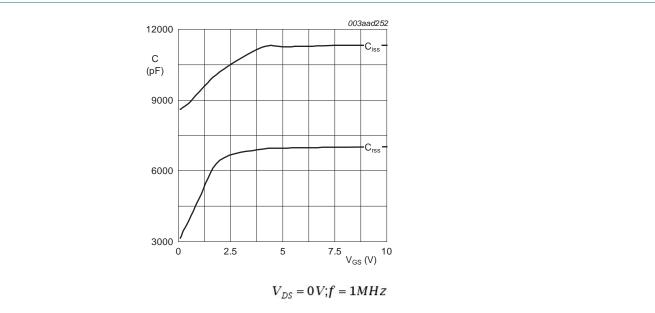


Fig 17. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

8. Package outline

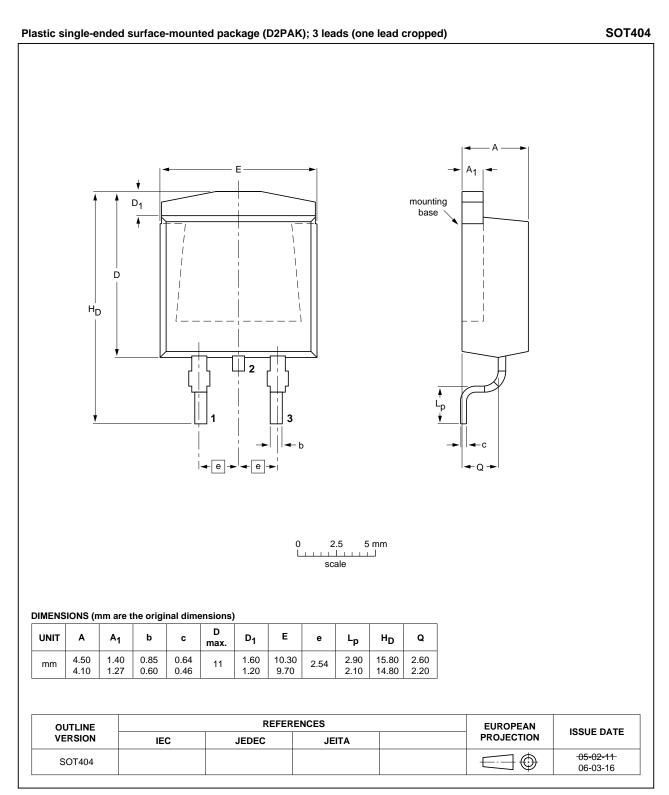


Fig 18. Package outline SOT404 (D2PAK)

9. Revision history

Table 8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|------------------|--------------|--------------------|---------------|------------|
| PSMN2R0-30BL v.1 | 20120320 | Product data sheet | - | - |

10. Legal information

10.1 Data sheet status

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|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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PSMN2R0-30BL

Nexperia

N-channel 30 V 2.1 mΩ logic level MOSFET in D2PAK

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